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Revisiting the measurement of the spin relaxation time in graphene-based spintronic devices HIROSHI IDZUCHI, CEMS, RIKEN, Japan, ALBERT FERT, Unité Mixte de Physique CNRS/Thales, France, YOSHICHIKA OTANI, ISSP, University of Tokyo, Japan — Spin transport in graphene has strongly drawn attention because of the expected long spin relaxation time τ sf, but, τ sf derived from experiments is rarely above 1 ns, shorter than theoretically expected and also largely dispersed [1]. Here we reanalyze Hanle curves in graphene-based lateral spin valves with various contacts by using the recently established model of Hanle effect taking into account the spin absorption by contacts [2]. We found the reanalysis of Hanle curves of four samples from transparent contacts to tunnel contacts, reported in ref.3, gives longer and much less dispersed τ sf ranging around 500 ps compared to the original values ranging from 84 ps to 495 ps. Extending our analysis to typical recent experiments with long spin diffusion length, $\lambda \sim 10 \ \mu m$, we find the spin absorption is even more pronounced because the contact resistance R needed to suppress the spin absorption scales with the spin resistance \propto λ . Thus R in the range of 100 kOhm is generally not large enough to suppress the spin absorption, and taking into account the contacts is more important to characterize the real τ sf in graphene with λ in this range.

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